

Features

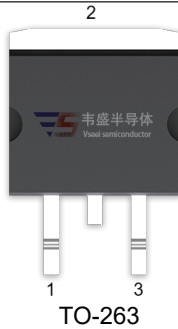
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant

Applications

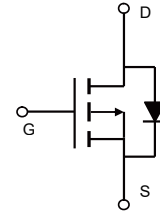
- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	-100	V
$V_{GS(th)}_{Typ}$	-1.7	V
$I_D(@V_{GS}=-10V)$	-56	A
$R_{DS(ON)}_{Typ}(@V_{GS}=-10V)$	18	m Ω
$R_{DS(ON)}_{Typ}(@V_{GS}=-4.5V)$	24	m Ω



TO-263



Schematic

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
VSM56P10-T3	VSM56P10	1	Tape&Reel	TO-263	800	4000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	-100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	A
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	423	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

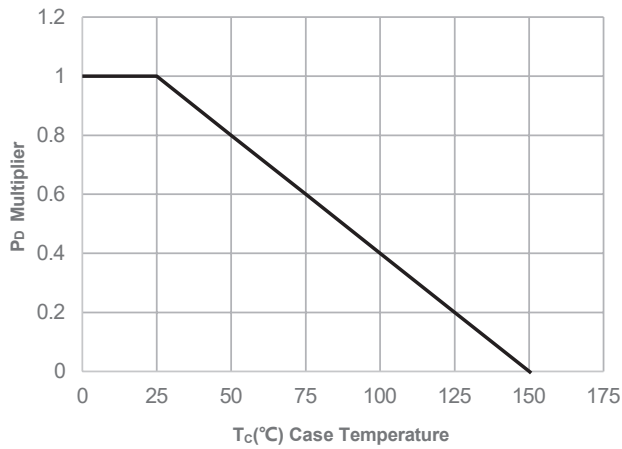
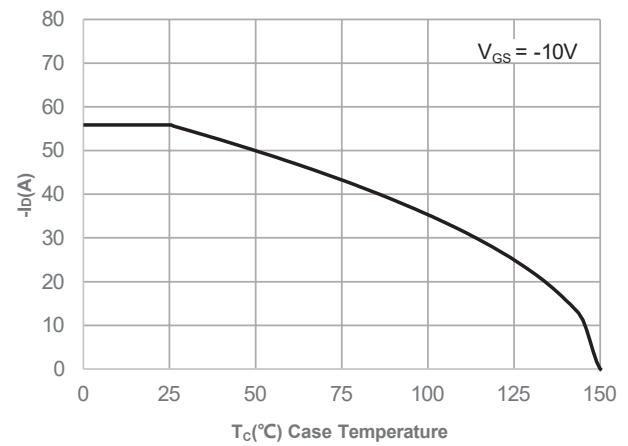
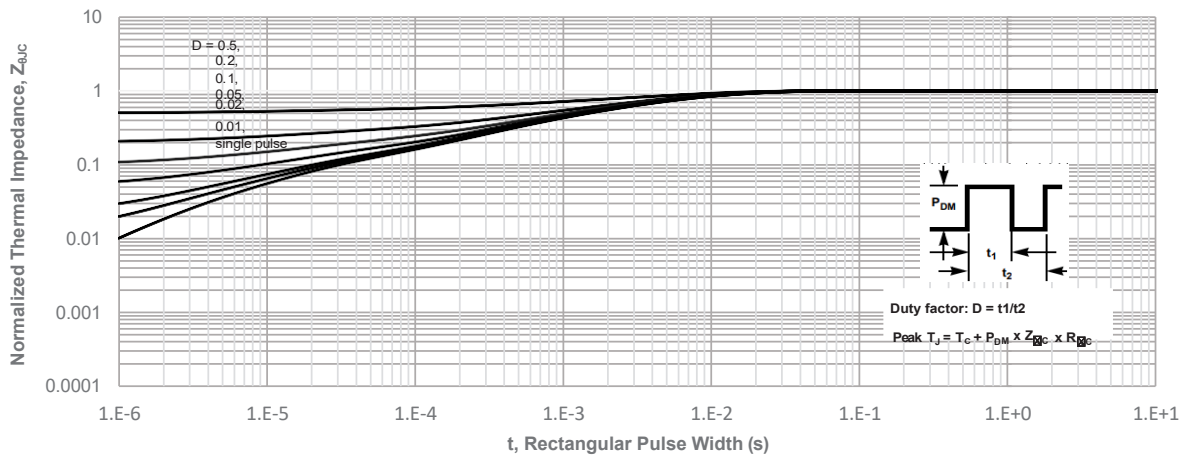
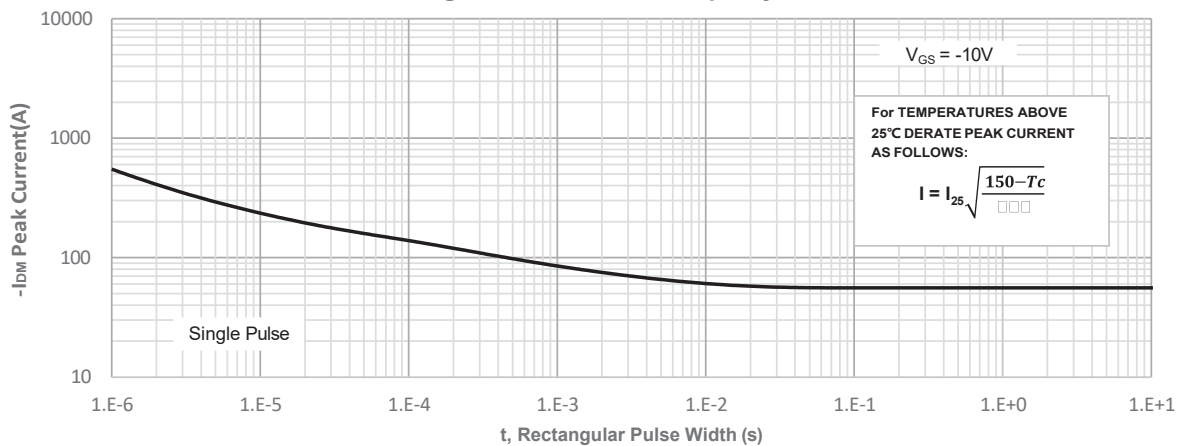
Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	36	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.9	

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

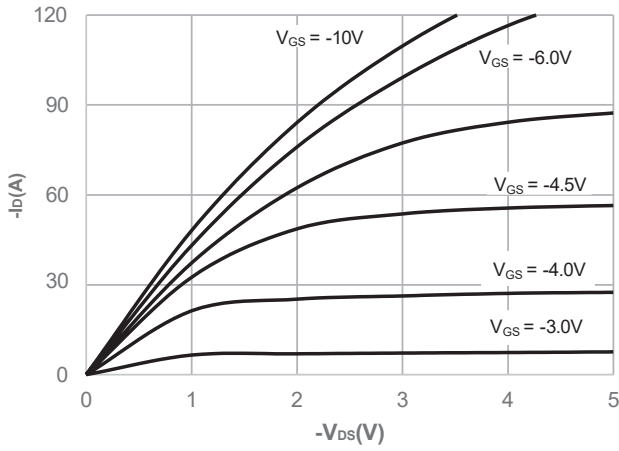
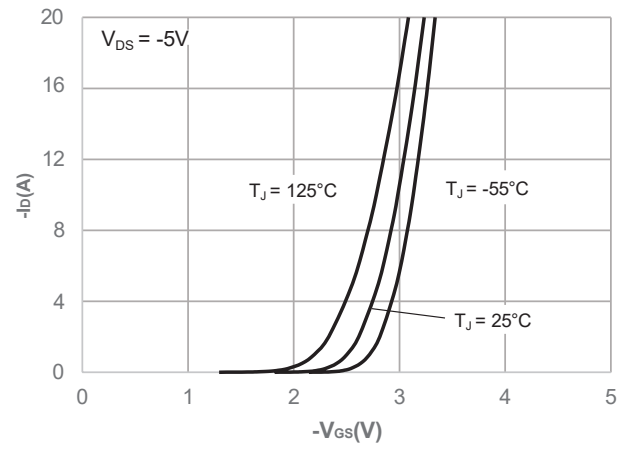
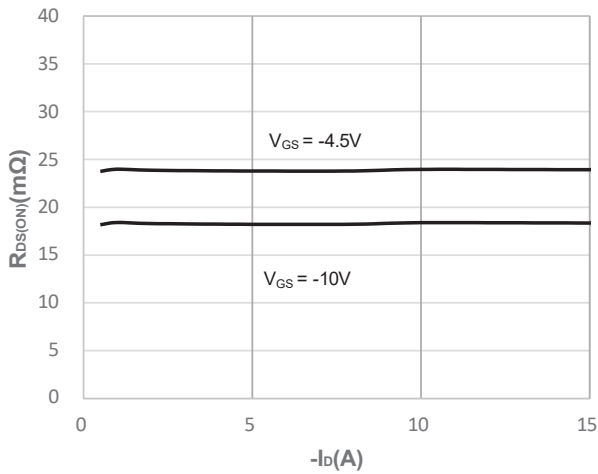
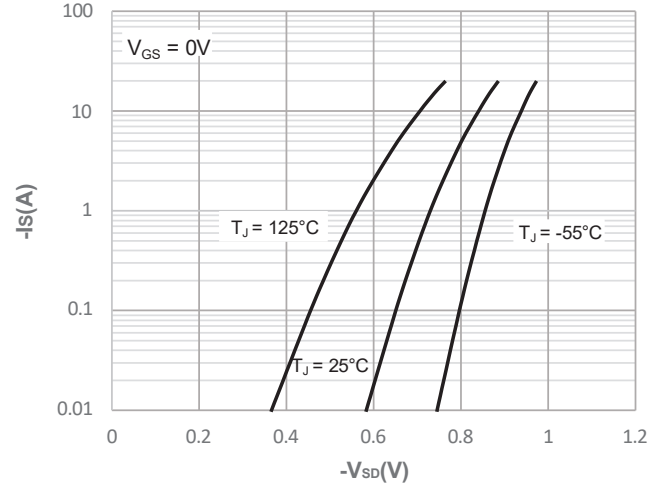
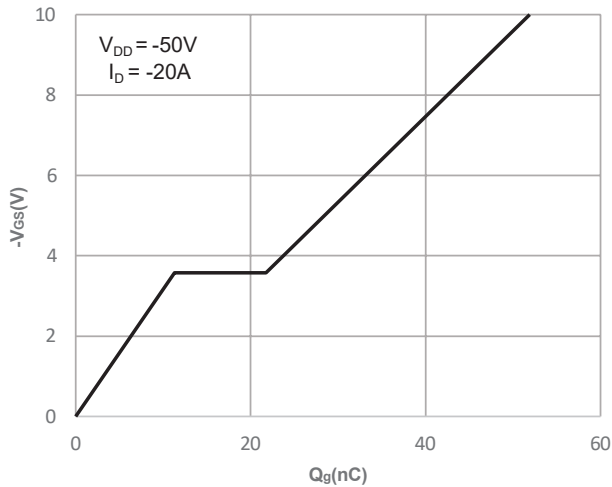
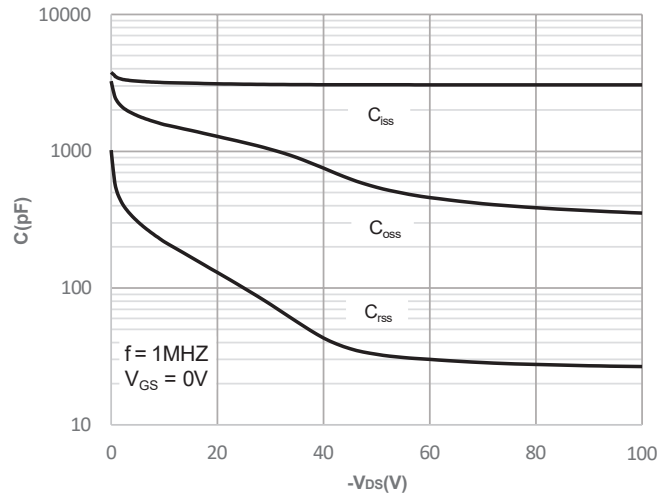
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = -250 μA, V _{GS} = 0V	-100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -80V, V _{GS} = 0V	-	-	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250 μA	-1.2	-1.7	-2.2	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = -10V, I _D = -20A	-	18	24	mΩ
		V _{GS} = -4.5V, I _D = -15A	-	24	31	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	3.4	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = -50V, f = 1MHz	2188	3063	4595	pF
C _{oss}	Output Capacitance		390	545	818	pF
C _{rss}	Reverse Transfer Capacitance		23	33	66	pF
Q _g	Total Gate Charge	V _{GS} = 0 to -10V V _{DS} = -50V, I _D = -20A	-	52	-	nC
Q _{gs}	Gate Source Charge		-	11	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	10	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = -10V, V _{DD} = -50V I _D = -20A, R _{GEN} = 3 Ω	-	10	-	ns
t _r	Turn-On Rise Time		-	25	-	ns
t _{d(off)}	Turn-Off DelayTime		-	51	-	ns
t _f	Turn-Off Fall Time		-	16	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	-56	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	-223	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = -20A	-		-1.2	V
trr	Body Diode Reverse Recovery Time	I _F = -20A, di/dt = 100A/us	47	65	98	ns
Qrr	Body Diode Reverse Recovery Charge		-	194	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = -50\text{V}$, $V_{GS} = -10\text{V}$, $R_G = 25\ \Omega$, $L = 3\text{mH}$, $I_{AS} = -16.8\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Power De-rating

Figure 2: Current De-rating

Figure 3: Normalized Maximum Transient Thermal Impedance

Figure 4: Peak Current Capacity


Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

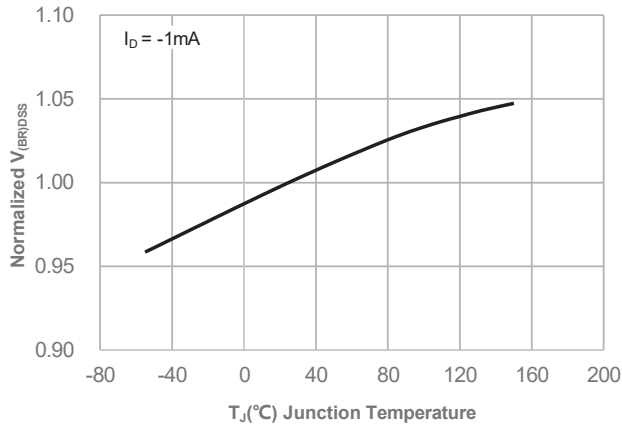


Figure 12: Normalized on Resistance vs. Junction Temperature

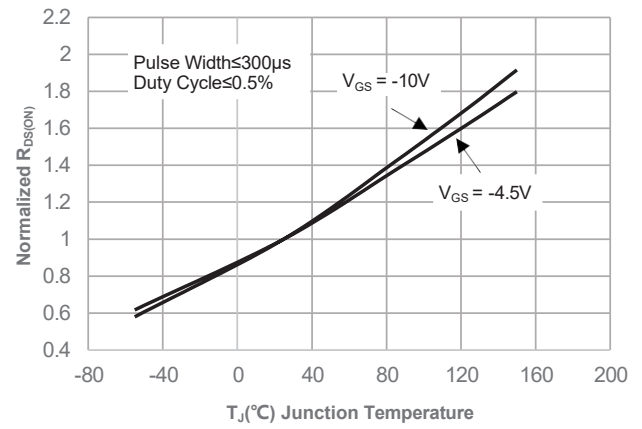


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

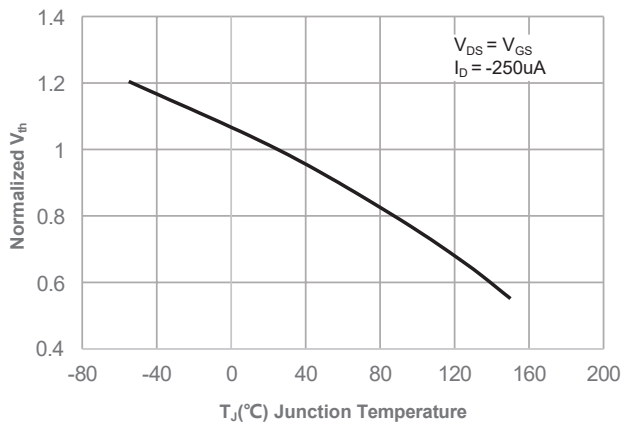


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

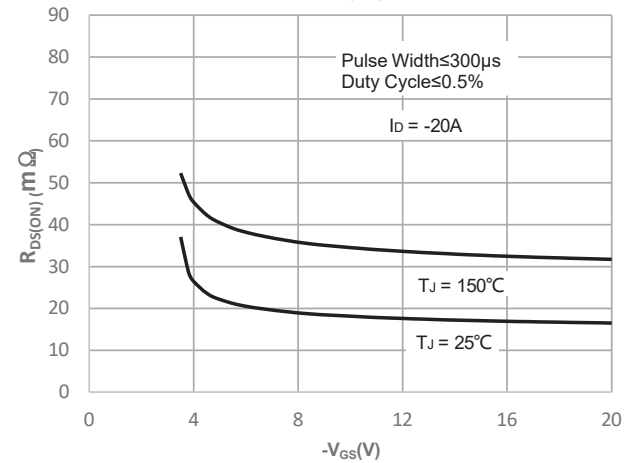
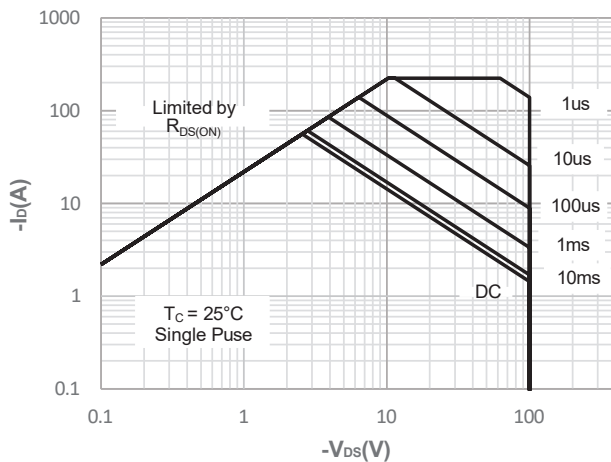


Figure 15: Maximum Safe Operating Area



Test Circuit

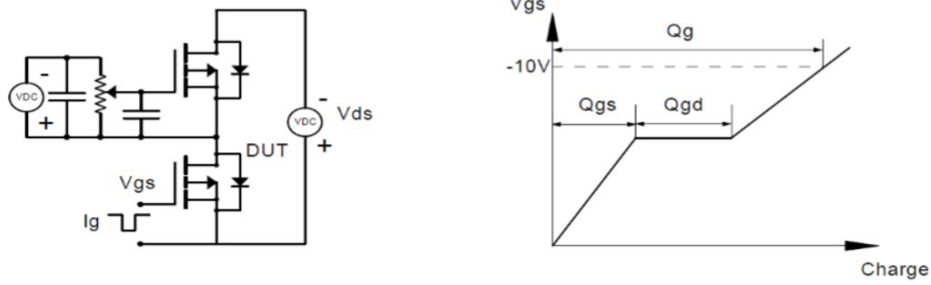


Figure 1: Gate Charge Test Circuit & Waveform

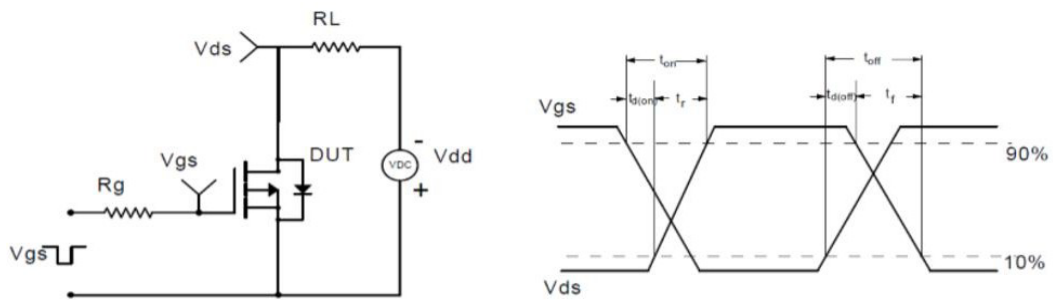


Figure 2: Resistive Switching Test Circuit & Waveform

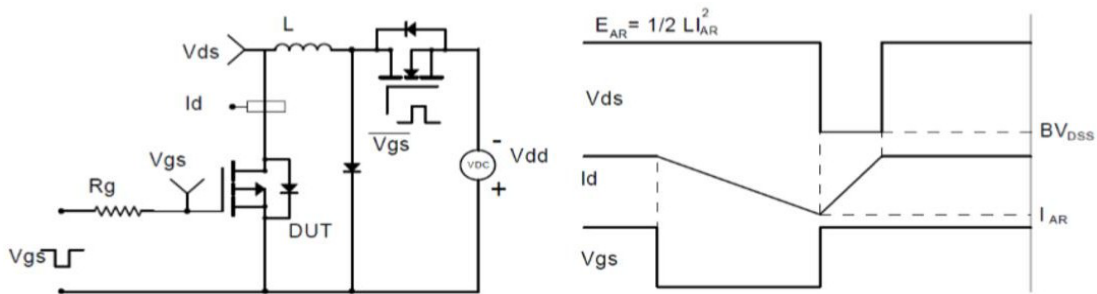


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

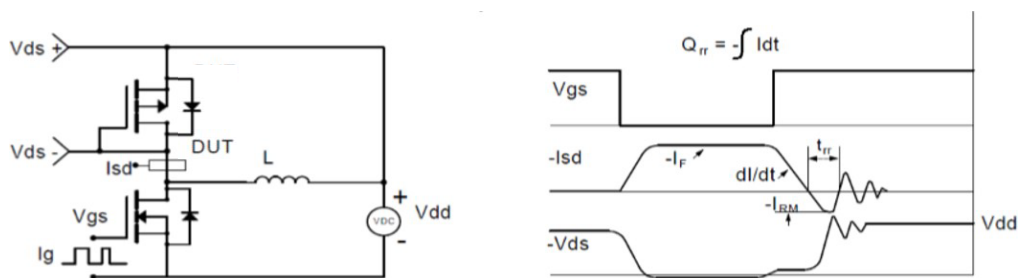


Figure 4: Diode Recovery Test Circuit & Waveform